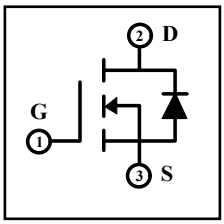
60A 30V N-channel Enhancement Mode Power MOSFET

1 Description

These N-channel enhancement mode power mosfets used advanced trench technology design, provided excellent Rdson and low gate charge. Which accords with the RoHS standard.



V_{DSS} =30V

$R_{DS(on)\ (TYP)}$=8.1mΩ

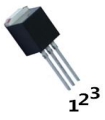
I_D =60A

2 Features

- Low on resistance
- Low gate charge
- Fast switching
- Low reverse transfer capacitances
- 100% single pulse avalanche energy test
- 100% ΔV_{DS} test

TO-220C

TO-220F



TO-262

TO-263

TO-252B

TO-251B

3 Applications

- Power switching applications
- Inverter management system
- Electric tools
- Automotive electronics

4 Electrical Characteristics

4.1 Absolute Maximum Ratings （Tc=25℃,unless otherwise noted）

Parameter		Symbol	Rating				Units
			DH081N03	DH081N03I DH081N03E	DH081N03B DH081N03D	DH081N03F	
Drian-to-Source Voltage		V_{DSS}	30				V
Gate-to-Source Voltage		V_{GSS}	±20				V
Continuous Drain Current	T_C=25℃	I_D	60				A
	T_C=100℃		42				A
Pulsed Drain Current(1)		I_{DM}	240				A
Single Pulse Avalanche Energy(4)		E_{AS}	83				mJ
Avalanche Current(4)		I_{AS}	18				A
Power Dissipation	T_a=25℃	P_{tot}	2	2	2	2	W
	T_C=25℃	P_{tot}	45	45	45	20	W
Isolation Voltage		V_{ISO}	2500				V
Junction Temperature Range		T_j	-55～175				℃
Storage Temperature Range		T_{stg}	-55～175				℃

4.2 Thermal Characteristics

Parameter	Symbol	Rating				Units
		DH081N03	DH081N03I DH081N03E	DH081N03B DH081N03D	DH081N03F	
Thermal Resistance,Junction to Case-sink	R_{thJC}	3.3	3.3	3.3	7.5	℃/W
Thermal Resistance,Junction to Ambient	R_{thJA}	75	75	75	75	℃/W

4.3 Electrical Characteristics (Tc=25℃,unless otherwise noted)

Parameter	Symbol	Test Condition	Value			Units
			Min	Typ	Max	
Off Characteristics						
Drain-to-Source Breakdown Voltage	BV_{DSS}	I_D=250μA,V_{GS}=0V	30	--	--	V
Drain-to-Source Leakage Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V,T_C=25℃	--	--	1	μA
		V_{DS}=30V,V_{GS}=0V,T_C=125℃	--	--	100	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1	1.5	2	V
Drain-to-Source on-state Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=30A	--	8.1	10	mΩ
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{GS}=0V,V_{DS}=30V,f=1.0MHz	--	848	--	pF
Output Capacitance	C_{oss}		--	125	--	
Reverse Transfer Capacitance	C_{rss}		--	105	--	
Gate Resisitance	R_G	V_{DD}=0V,V_{GS}=0V,F=1MHz	--	2.06	--	Ω
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	I_D=30A, V_{DD}=15V, V_{GS}=10V, R_{GEN}=25Ω	--	7.3	--	nS
Turn-on Rise Time	t_r		--	91	--	
Turn-off Delay Time	$t_{d(off)}$		--	68	--	
Turn-off Fall Time	t_f		--	94	--	
Total Gate Charge	Q_g	I_D=30A,V_{DD}=15V,V_{GS}=10V	--	20	--	nC
Gate-to-Source Charge	Q_{gs}		--	4.75	--	
Gate-to-Drain(“Miller”) Charge	Q_{gd}		--	4.66	--	
Drain-Source Diode Characteristics						
Diode Forward Voltage(3)	V_{SD}	V_{GS}=0V,I_S=30A	--	--	1.3	V
Diode Forward Current	I_S		--	--	60	A
Reverse Recovery Time(3)	t_{rr}	T_J=25℃,I_F=30A, dI_F/dt=100A/μS,V_{GS}=0V	--	3.6	--	nS
Reverse Recovery Charge(3)	Q_{rr}		--	0.54	--	nC

Notes：

1: Repetitive rating, pulse width limited by maximum junction temperature.

2: Surface mounted on FR4 Board, t≤10sec.

3: Pulse width ≤ 300μs, duty cycle ≤ 2%.

4: L=0.5mH,I_D=18A,V_{DD}=24V,V_{GATE}=30V,Start T_J=25℃.

5 Typical characteristics diagrams

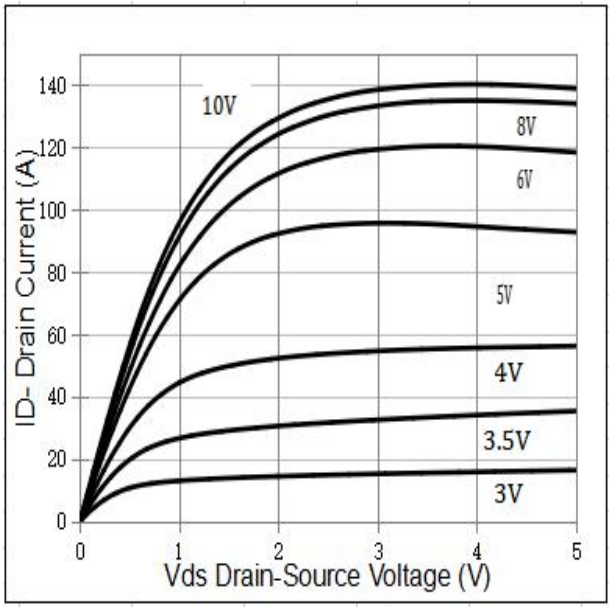


Figure 1 Output Characteristics

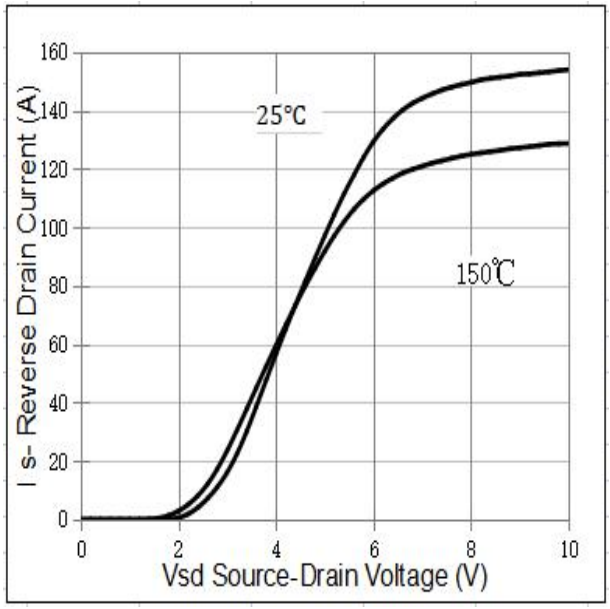


Figure 2 Transfer Characteristics

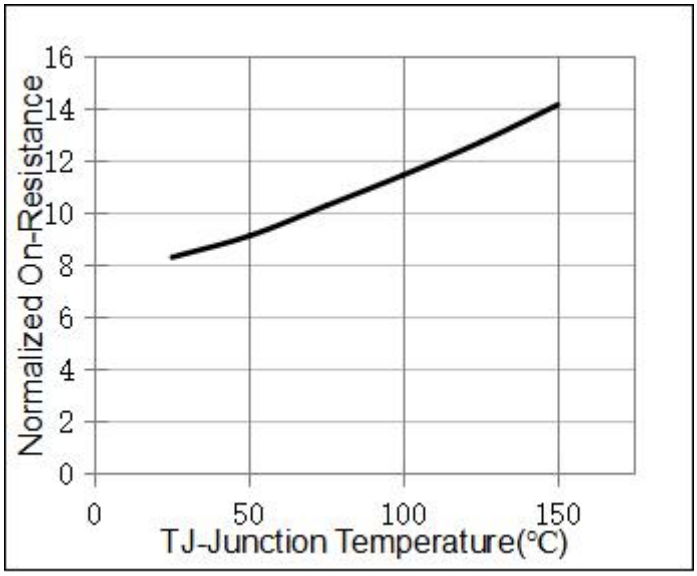


Figure 3. Rdson vs Temperature

5 Typical characteristics diagrams(continues)

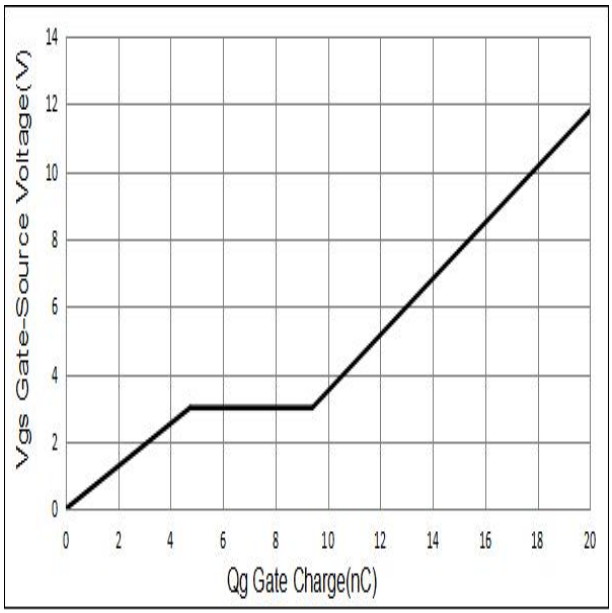


Fig 5. Gate Charge

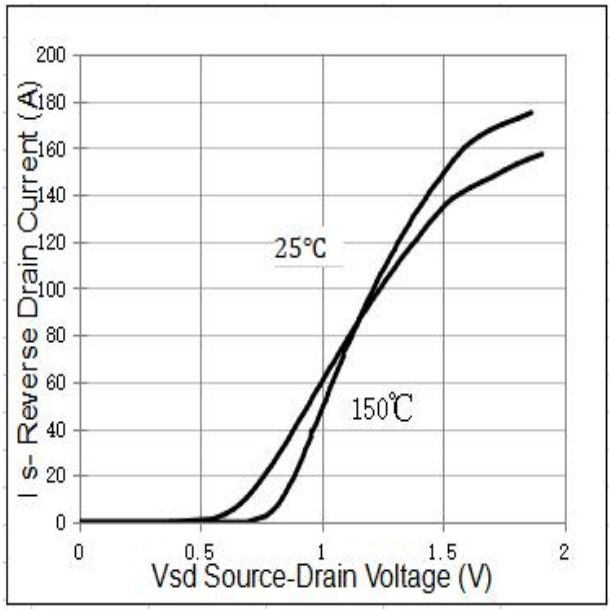


Fig 6. Source-Drain Diode Forward

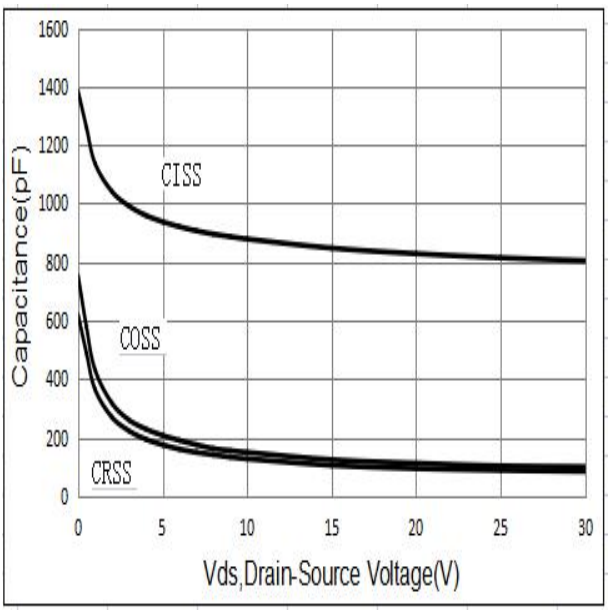


Figure 7. Capacitance Characteristics

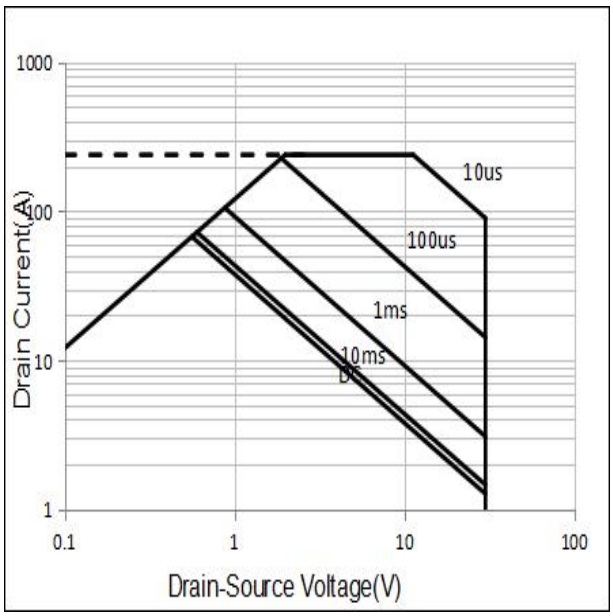


Figure 8. Gate Charge Characteristics

5 Typical characteristics diagrams(continues)

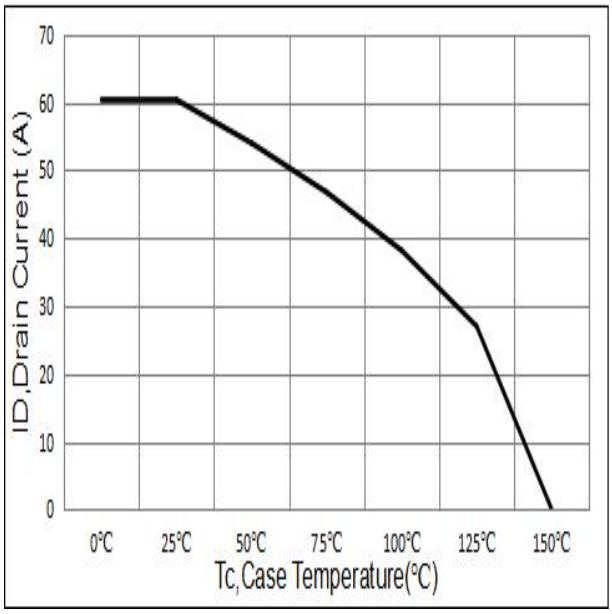


Figure 9. ID Current De-rating

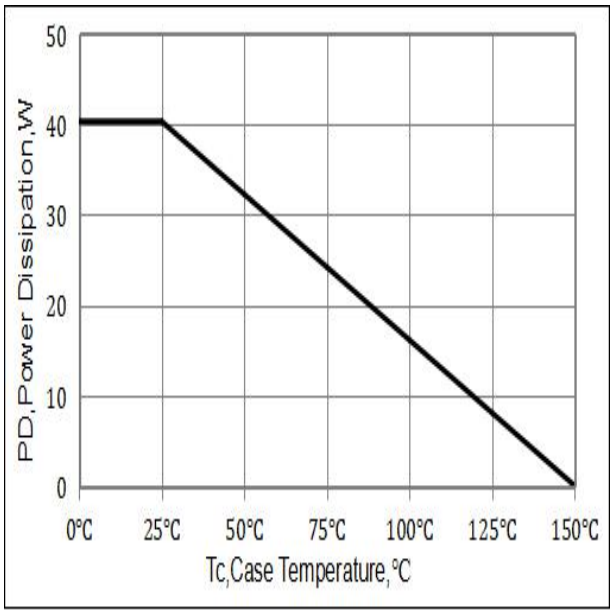


Figure 10. Power De-rating

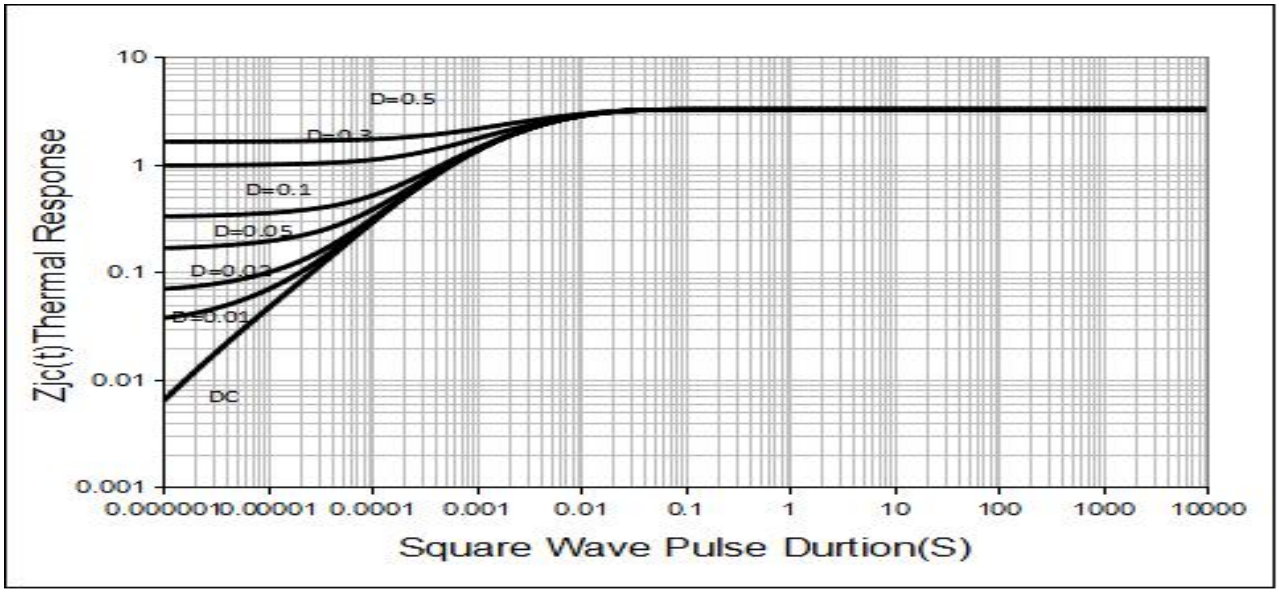
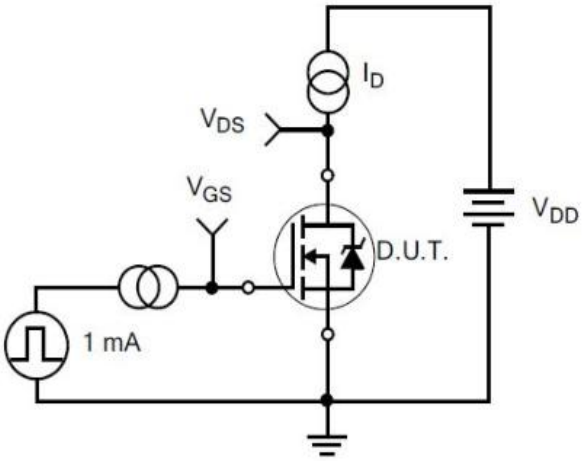
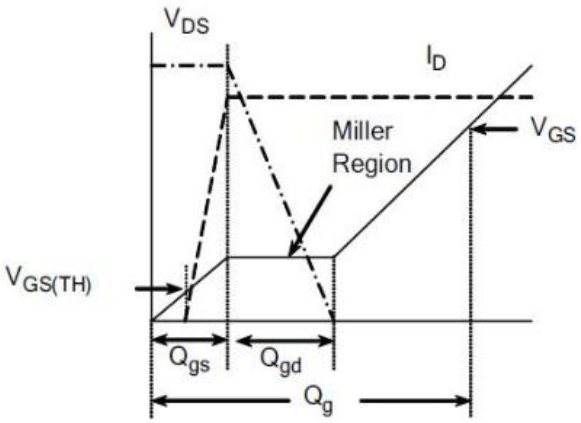


Fig 11. Normalized Maximum Transient Thermal Impedance

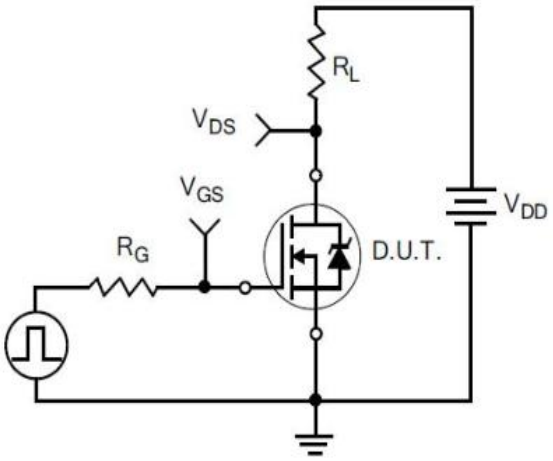
6 Typical Test Circuit and Waveform



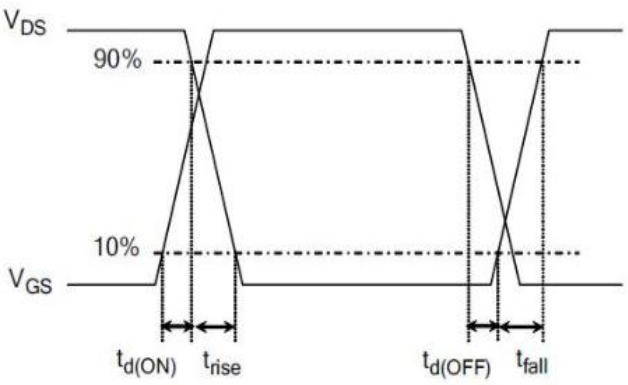
1) Gate Charge Test Circuit



2) . Gate Charge Waveform

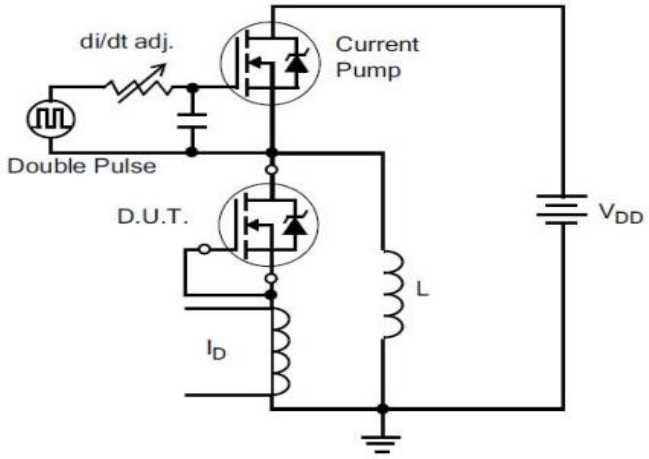


3) Resistive Switching Test Circuit

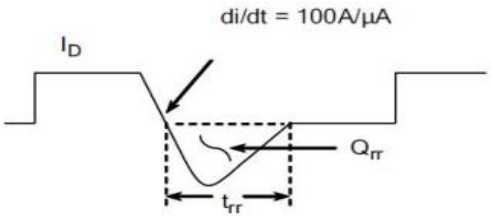


4) Resistive Switching Waveforms

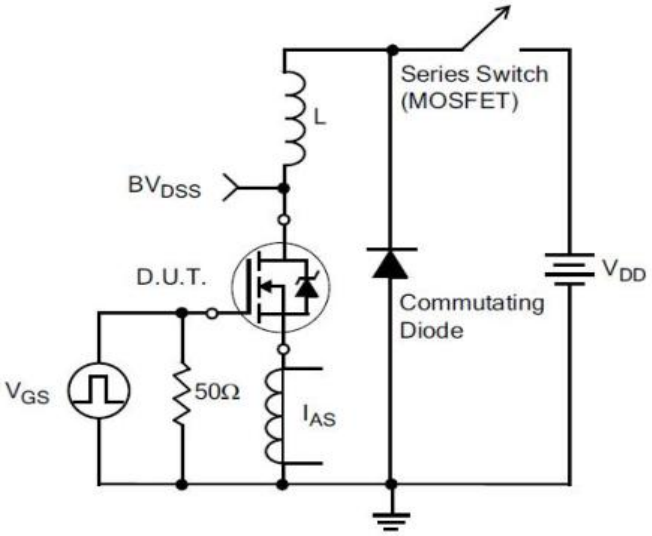
6 Typical Test Circuit and Waveform(continues)



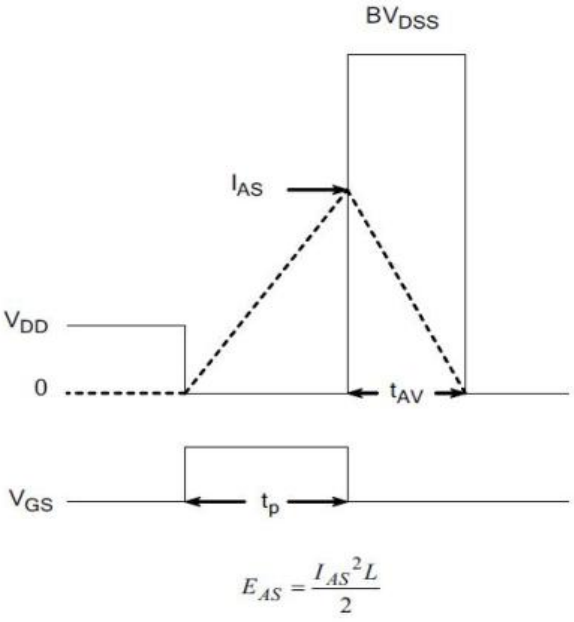
5) Diode Reverse Recovery Test Circuit



6) Diode Reverse Recovery Waveform



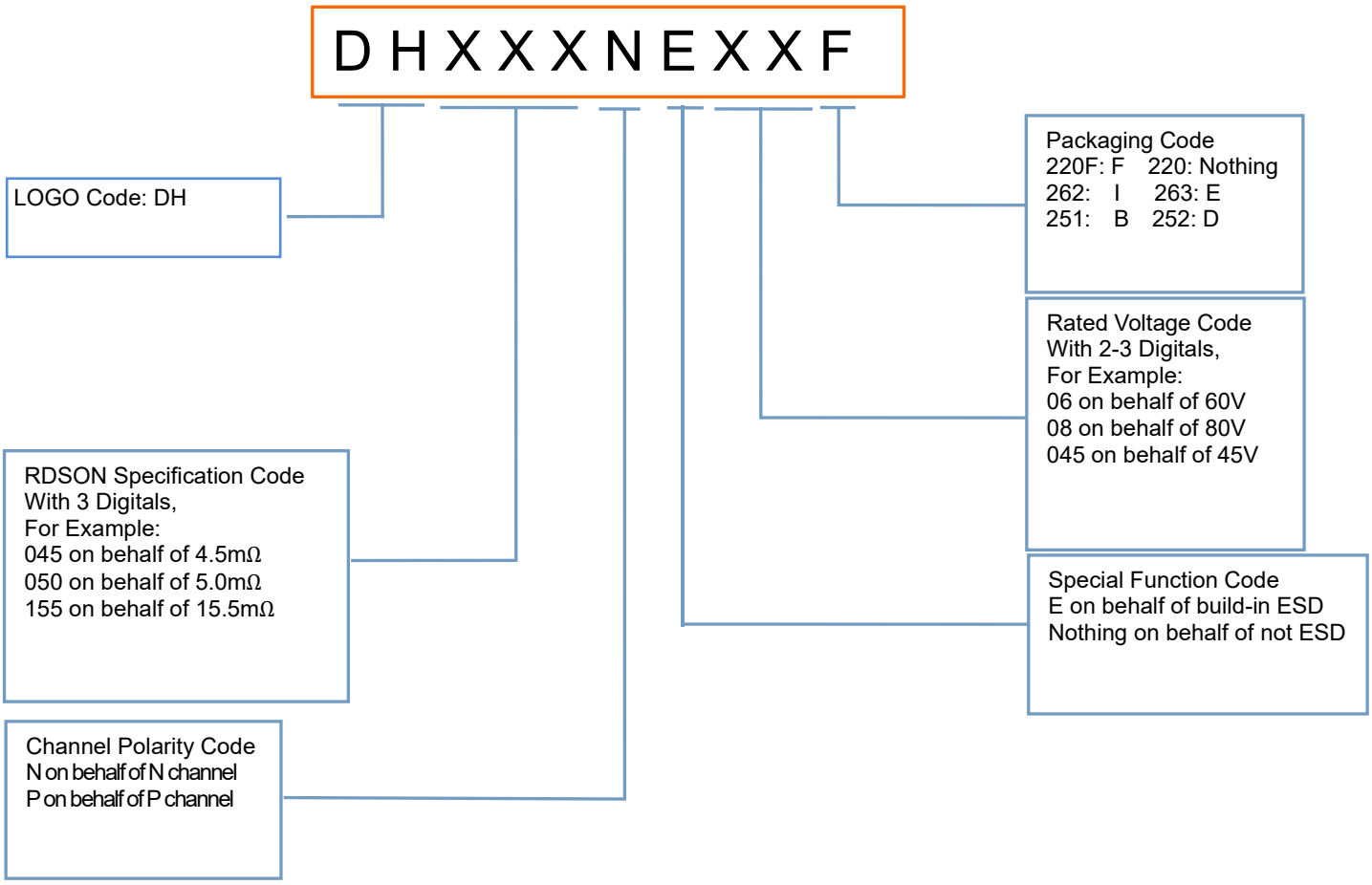
7) . Unclamped Inductive Switching Test Circuit



$$E_{AS} = \frac{I_{AS}^2 L}{2}$$

8) Unclamped Inductive Switching Waveforms

7 Product Names Rules

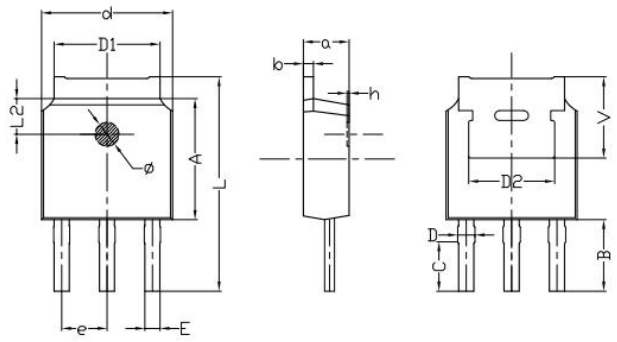


8 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
DH081N03	TO-220	DH081N03	Pb-free	Tube	1000/box
DH081N03F	TO-220F	DH081N03F	Pb-free	Tube	1000/box
DH081N03B	TO-251	DH081N03B	Pb-free	Tube	3000/box
DH081N03D	TO-252	DH081N03D	Pb-free	Tape & Reel	2500/box
DH081N03I	TO-262	DH081N03I	Pb-free	Tube	1000/box
DH081N03E	TO-263	DH081N03E	Pb-free	Tape & Reel	800/box

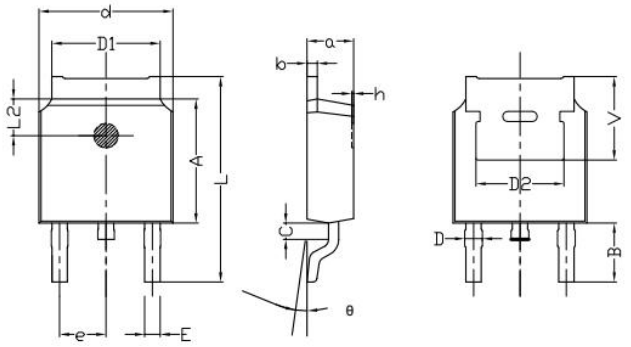
9 Dimensions

TO-251B PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
a	2.20	2.40	0.087	0.0946
b	0.46	0.58	0.018	0.023
C	2.45	2.65	0.097	0.104
D	0.80	0.90	0.032	0.035
d	6.30	6.70	0.248	0.264
D1	5.00	5.50	0.197	0.217
D2	TYP 4.83		TYP 0.190	
A	5.80	6.20	0.228	0.244
e	2.19	2.39	0.086	0.094
L	10.40	11.00	0.4098	0.4334
B	3.50	3.70	0.1379	0.1458
L2	1.5	1.8	0.059	0.071
Φ	1.10	1.30	0.0433	0.0512
h	0.00	0.30	0.000	0.012
V	5.25	5.85	0.207	0.230
E	0.60	0.80	0.0236	0.0315

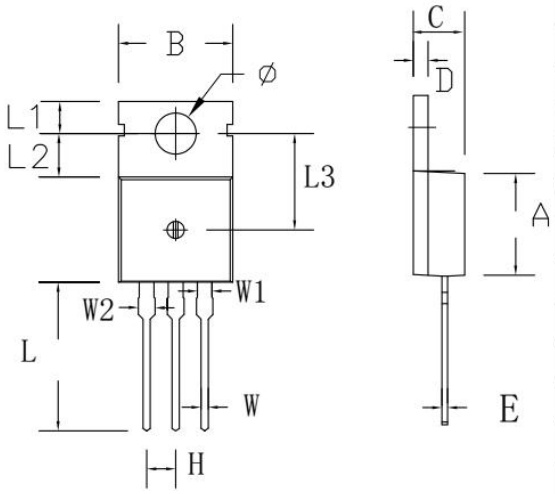
TO-252B PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
a	2.20	2.40	0.087	0.095
b	0.46	0.58	0.018	0.023
c	0.70	0.90	0.028	0.035
D	0.80	1.00	0.032	0.039
d	6.30	6.70	0.248	0.264
D1	5.00	5.50	0.197	0.217
D2	TYP 4.83		TYP 0.190	
A	5.80	6.20	0.228	0.244
e	2.19	2.39	0.086	0.094
L	9.40	10.40	0.370	0.409
B	2.6	3.2	0.102	0.126
L2	1.5	1.8	0.059	0.071
θ	0	8	0	8
h	0	0.3	0	0.012
V	5.25	5.85	0.207	0.230
E	0.6	0.8	0.024	0.032

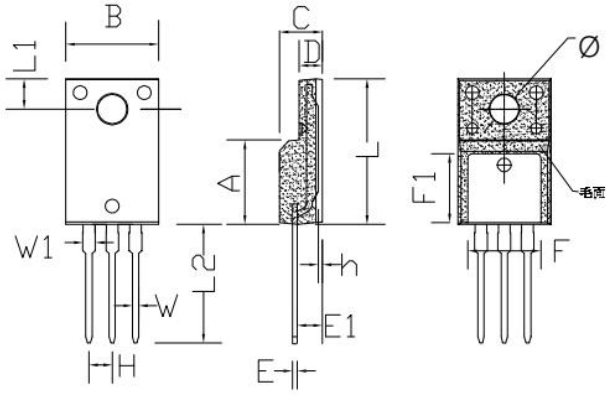
9 Dimensions(continues)

TO-220C PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	9.70	10.30	0.382	0.406
C	4.25	4.75	0.167	0.187
D	1.20	1.45	0.047	0.057
E	0.40	0.60	0.016	0.024
H	2.54 TYP		0.100 TYP	
W	0.60	0.95	0.024	0.037
W1	1.05	1.45	0.041	0.057
W2	1.20	1.60	0.047	0.063
L	12.60	13.40	0.496	0.528
L1	2.45	2.95	0.096	0.116
L2	3.45	3.95	0.136	0.156
L3	8.15	8.65	0.321	0.341
Φ	3.50	3.90	0.138	0.154

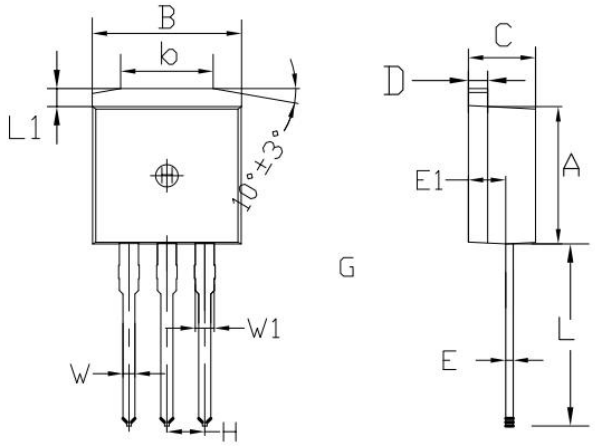
TO-220F PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	10.00	10.50	0.394	0.413
C	4.30	4.90	0.169	0.193
D	2.30	2.70	0.091	0.106
L	15.55	16.15	0.612	0.636
h	0.40	0.60	0.016	0.024
L1	3.15	3.55	0.124	0.140
L2	12.65	13.35	0.498	0.526
W	0.70	0.90	0.028	0.035
W1	1.15	1.55	0.045	0.061
H	2.54 TYP		0.100 TYP	
E	0.48	0.53	0.019	0.021
Φ	2.90	3.40	0.114	0.134
E1	2.40	2.90	0.094	0.114
F	7.75	8.25	0.305	0.325
F1	7.35	7.85	0.289	0.309

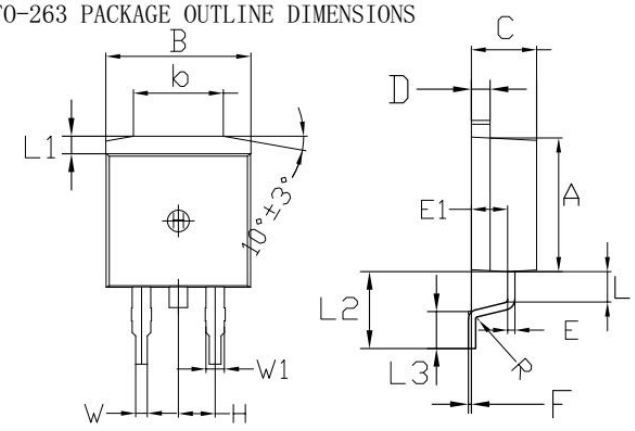
9 Dimensions(continues)

TO-262 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	9.70	10.30	0.382	0.406
C	4.25	4.75	0.167	0.187
D	1.20	1.45	0.047	0.057
E	0.40	0.60	0.016	0.024
L	12.25	13.75	0.482	0.541
L1	1.15	1.45	0.045	0.057
E1	2.4	2.6	0.0945	0.1024
W	0.80	0.82	0.0315	0.034
W1	1.20	1.30	0.047	0.051
H	2.54 TYP		0.200 TYP	
b	5.50	6.50	0.216	0.256

TO-263 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	9.70	10.30	0.382	0.406
C	4.25	4.75	0.167	0.187
D	1.20	1.45	0.047	0.057
E	0.40	0.60	0.016	0.024
L	1.90	2.30	0.075	0.091
L1	1.15	1.45	0.045	0.057
R	0.24	0.26	0.0095	0.0102
W	0.80	0.82	0.0315	0.0323
W1	1.20	1.30	0.047	0.051
H	2.54 TYP		0.200 TYP	
b	5.50	6.50	0.216	0.256
E1	2.4	2.6	0.0946	0.1024
L2	5.20	5.80	0.205	0.228
L3	2.20	3.20	0.087	0.126
F	0.03	0.23	0.0012	0.0091

10 Attentions

- Jiangsu Donghai Semiconductor Technology CO.,LTD. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Donghai products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

11 Appendix

Revision history:

Date	REV.	Description	Page
2021.04.06	1.0	Original	